

**ESD TR5.5-04-22**

# **ESD Association Technical Report**

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*For Electrostatic Discharge  
Sensitivity Testing*

*Transmission Line Pulse (TLP) –  
User and Application Guide*

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## **FOREWORD**

This document was prepared by the EOS/ESD Association, Inc. Working Group 5.5, Transmission Line Pulse. It is intended as a compilation for the standard test method document describing the transmission line pulse (TLP) method: ANSI/ESD STM5.5.1.

This document consists of user guides and application guides.

The user guides are short sections dealing with a single aspect of the setup, configuration, or calibration of TLP equipment. Each section can be read and used on its own and serves as a clarification of the basics covered in the ANSI/ESD STM5.5.1.

The structure of each section is basically the same. The topic is introduced and discussed in more detail. Selected examples are provided to demonstrate the discussed subject. The section is closed by providing a list of the most relevant references for further study.

The application guides are short sections dealing with possible use cases of TLP and TLP data. Each section can be read and used on its own and serves as a clarification of how a TLP setup, following the best practices discussed in the user guides, can be used to answer several different questions.

The structure of each section generally follows the structure of the user guides. The topic is introduced and discussed in more detail. Selected examples are provided to demonstrate the discussed application, typically using published data. The section is closed by providing a list of the most relevant references for further study.

This technical report<sup>1</sup> was originally designated ESD TR5.5-01-18 and published on June 1, 2018. ESD TR5.5-04-21 is a revision of ESD TR5.5-01-18 and published on October 15, 2021.

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<sup>1</sup> **ESD Association Technical Report (TR):** A collection of technical data or test results published as an informational reference on a specific material, product, system, or process.

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**TABLE OF CONTENTS**

**1.0 INTRODUCTION ..... 1**

    1.1 PURPOSE ..... 1

    1.2 SCOPE ..... 1

**2.0 USER GUIDES ..... 1**

    2.1 CONTACT AND GROUNDING ISSUES DURING TLP TESTING ..... 2

    2.2 OSCILLOSCOPE CORRECTIONS ..... 6

    2.3 TLP CALIBRATION..... 7

    2.4 BURN-IN, INITIAL PULSES TO REDUCE CONTACT RESISTANCE ..... 11

    2.5 TEST FIXTURES ..... 13

    2.6 MEASUREMENT WINDOW SELECTION..... 15

    2.7 BIASED TLP MEASUREMENTS ..... 18

    2.8 TLP LOAD LINES AND SNAPBACK DEVICES ..... 23

    2.9 RISE TIME VERIFICATION AND REPORTING ..... 28

    2.10 TLP VOLTAGES ..... 33

**3.0 APPLICATION GUIDES ..... 35**

    3.1 CORRELATION BETWEEN HBM AND TLP ..... 35

    3.2 CORRELATION BETWEEN TLP AND ESD SYSTEM LEVEL STRESS ..... 37

    3.3 CHARACTERIZATION FOR SYSTEM EFFICIENT ESD DESIGN (SEED)..... 40

    3.4 POWER PROFILE TLP ..... 42

    3.5 MOS SAFE OPERATING AREA CHARACTERIZATION USING TLP ..... 44

    3.6 GATE OXIDE CHARACTERIZATION..... 47

    3.7 STOP & GO TLP ..... 50

    3.8 REPETITIVE TLP ..... 52

**Annexes**

Annex A (Informative): Revision History for ESD TR5.5-04 ..... 54

**Tables**

Table 1: Calculations of TLP Impedance Using a 200-Volt TLP Voltage, 50-Ohm  $R_{Cable}$ ,  
500-Ohm  $R_{Series}$ , and 50-Ohm  $R_{Scope}$  ..... 26

**Figures**

Figure 1: Basic Connection Scheme ..... 2

Figure 2: 4-Point-Kelvin Connection Scheme ..... 3

Figure 3: Connection Scheme with Additional DC Bias Signals ..... 4

Figure 4: Voltage Transients Measured with and Without Correct Ground Connection ..... 5

Figure 5: TLP I-V Curves of a 5-Ohm Resistor before and after Signal Path Compensation ..... 6

Figure 6: Uncorrected TLP Data..... 7

Figure 7: Components in Blue Dealt with by the Correction ..... 8

Figure 8: Circuit Models of Correction Needed .....	8
Figure 9: Correction Rotation and Calibration Stretching Data Points .....	9
Figure 10: Components in Orange Dealt with by the Calibration .....	9
Figure 11: Typical I-V Plot of Short (Blue Curve) Calibration Caused by Oxides on Tungsten Needles.....	11
Figure 12: Typical I-V Plot of Short Calibration with Osmium Tip Needles .....	12
Figure 13: Coaxial RF Probe with a Single Probe Needle for the Signal with a Clip and Flexible Connector Connected to a Second Probe Needle to be Used for the Ground Connection.....	13
Figure 14: Example of Wafer Probes for Carrying a Balanced TLP Signal to Two Wafer Probe Needles .....	14
Figure 15: Comparison of the Same 100 ns TLP Data on a 1-Ohm Resistor Using a Single Point, 7 Points Over in a 2.8 ns Window, and 51 Points in a 20 ns Window .....	15
Figure 16: Example of Waveform with Ringing and Suggested Measurement Window .....	16
Figure 17: Sample of TLP I-V Curves Taken with Different Time Windows.....	17
Figure 18: Illustration of the Problem of Applying a TLP Stress to a Biased Node and use of a Bias Tee to Overcome the Problems.....	18
Figure 19: Configuration A - Kelvin or Pseudo Kelvin Measurement in Which the Voltage Probe is on the DUT side of the Bias Tee; Configuration B – a TDR Setup in Which the Voltage and Current Probes are on the TLP Pulse Source Side of the Bias Tee .....	19
Figure 20: TDR TLP Measurements of a Zener Diode Without a Bias Tee and with a Bias Tee with Voltages of 0 to 5 Volts Without Correction Factors .....	20
Figure 21: TDR TLP Measurements of a Zener Diode Without a Bias Tee and with a Bias Tee with Voltages of 0 to 5 volts with Correction for Bias Voltage but not for Voltage Build up Across the Capacitor or Resistance in the Bias Tee .....	20
Figure 22: TDR TLP Measurements of a Zener Diode Without a Bias Tee and with a Bias Tee with Voltages of 0 to 5 Volts with Correction for Bias Voltage and Voltage Across the Bias Tee but no Correction for Resistance in the Bias Tee .....	21
Figure 23: TDR TLP Measurements of a Zener Diode Without a Bias Tee and with a Bias Tee with Voltages of 0 to 5 Volts with all Corrections.....	21
Figure 24: Kelvin TLP Measurements of a Zener Diode with and Without a Bias Tee with Voltages of 0 to 5 Volts with no Corrections Needed .....	22
Figure 25: Equivalent Circuit for a TLP Tester .....	23
Figure 26: Three Load Line Examples for Several DUT Resistances.....	24
Figure 27: Schematics of Two TLP Systems with Different Impedances.....	25
Figure 28: Schematics for Calculating Load Line Resistance .....	25
Figure 29: Low-Current TLP Measurements of a TVS with a Large Snap-back Using Both a Standard TDR System and a High Impedance System .....	27
Figure 30: 5 ns-TLP Pulses Normalized for Voltage Plateau Amplitude Showing the Rise Time Dependence on Pulse Voltage .....	28
Figure 31: TLP Pulses Normalized for Voltage Amplitude Showing the Rise Time Dependence on Pulse Width.....	29
Figure 32: Wiring Diagram for Pulse Source Verification .....	29
Figure 33: TLP Pulses Normalized for Voltage Amplitude Showing the Dependence of Rise Time on the Type of Probes .....	30
Figure 34: Wiring Diagram for Verifying the Risetime at the Output on the Pulse Delivery Setup .....	31
Figure 35: Flow Chart for Reporting Rise Time Evaluation .....	32
Figure 36: Basic Time Domain Reflection TLP System .....	33

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Figure 37: Time Domain Reflection TLP System with 50-Ohm Load.....	34
Figure 38: Time Domain Reflection TLP System with an Open Load.....	34
Figure 39: Correlation Plots of HBM Failure Voltage and TLP Failure Current .....	36
Figure 40: ESD System Level Stress Pulses with Two Different Discharge Networks .....	37
Figure 41: High-Current Characterization of DP USB Signal Pin.....	41
Figure 42: TLP Characteristics with Different Pulse Durations .....	42
Figure 43: Power-to-Failure vs. Pulse Duration .....	43
Figure 44: Gate Bias Setup for Electrical SOA Measurements.....	44
Figure 45: Gate Bias Setup for Electrical SOA Measurements.....	45
Figure 46: MV NMOS device SOA characterization.....	45
Figure 47: HV NMOS device SOA characterization .....	45
Figure 48: Schematic Representation of the Three Main Different Characterization Methods of Gate Oxides.....	47
Figure 49: Set-up Configuration Used for the Gate Oxide Time Dependent Dielectric Breakdown Experiments.....	48
Figure 50: Pulse Waveform for a 4.64-Volt Stress Sensed at the Gate.....	48
Figure 51: Voltage Acceleration for nFET at 25°C .....	49
Figure 52: Three Consecutive TLP Runs on a Polysilicon Resistor.....	50
Figure 53: TLP Characteristics of Two Consecutive Runs on the Same DUT.....	51
Figure 54: Step Size Effect in 1 ns (VF-)TLP Testing on LVTSCR; and 100 ns-TLP Characteristics for 2 HV ggNMOSTs, One of Which Shows a Clear Progressive Soft Leakage.....	52
Figure 55: Leakage Current vs. Number of Pulses at 3 Fixed Current Levels for the ggNMOSTs of Figure 54; and Wear Out Effect in Metal Line Resulting from Repetitive 100 ns TLP Stress .....	53
Figure 56: Wear-Out Plot - Failure Level vs. Number of Pulses .....	53

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**ESD Association Technical Report for Electrostatic Discharge Sensitivity Testing – Transmission Line Pulse (TLP) – User and Application Guide**

**1.0 INTRODUCTION**

**1.1 Purpose**

The information and procedures explained in this technical report are intended to help those performing transmission line pulse (TLP) testing as described in ANSI/ESD STM5.5.1 - ESD Association Standard Test Method for Electrostatic Discharge (ESD) Sensitivity Testing – Transmission Line Pulse (TLP) – Device Level<sup>2</sup>.

**1.2 Scope**

The document is divided into two main sections: the user guide which focuses on setting up and calibrating the TLP system; and the application guide which focuses on possible methods of using TLP.

It is expected that subsequent versions of this document will be released that expand the coverage of the user and application guides. Since this document is a companion to ANSI/ESD STM5.5.1, it is limited to the quasi-static application of TLP. Other applications of TLP will be described in separate documents.

**2.0 USER GUIDES**

The user guides are short sections dealing with a single aspect of the setup, configuration, or calibration of TLP equipment. Each section can be read and used on its own and serves as a clarification of the basics covered in the ANSI/ESD STM5.5.1.

The structure of each section is basically the same. The topic is introduced and discussed in more detail. Selected examples are provided to demonstrate the discussed subject. The section is closed by providing a list of the most relevant references for further study.

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